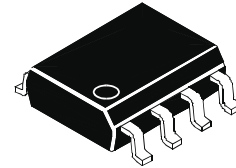


30V P-CHANNEL ENHANCEMENT MODE MOSFET**SUMMARY** **$V_{(BR)DSS}=-30V$; $R_{DS(ON)}=0.025\Omega$; $I_D=-7.9A$** **DESCRIPTION**

This new generation of high density MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



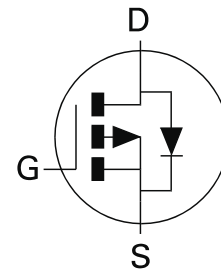
SO8

FEATURES

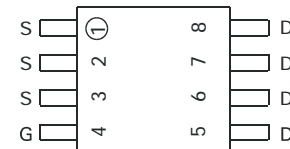
- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Disconnect switches
- Motor control

**ORDERING INFORMATION**

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXM66P03N8TA	7"	12mm	500 units
ZXM66P03N8TC	13"	12mm	2500 units



Top View

DEVICE MARKING

- ZXM6
6N03

ZXM66P03N8

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=-10V; T_A=25^{\circ}C(b)$ $V_{GS}=-10V; T_A=70^{\circ}C(b)$ $V_{GS}=-10V; T_A=25^{\circ}C(a)$	I_D	-7.9 -6.3 -6.25	A
Pulsed Drain Current (c)	I_{DM}	-28	A
Continuous Source Current (Body Diode)(b)	I_S	-4.1	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	-28	A
Power Dissipation at $T_A=25^{\circ}C$ (a) Linear Derating Factor	P_D	1.56 12.5	W mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b) Linear Derating Factor	P_D	2.5 20	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_J; T_{stg}$	-55 to +150	$^{\circ}C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	80	$^{\circ}C/W$
Junction to Ambient (b)	$R_{\theta JA}$	50	$^{\circ}C/W$

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.05$, pulse width $10\mu s$ - pulse width limited by maximum junction temperature.



ZXM66P03N8

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			-1	μA	$V_{DS} = -24\text{V}$, $V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}			-100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	$I_D = -250\mu\text{A}$, $V_{DS} = V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.025 0.035	Ω Ω	$V_{GS} = -10\text{V}$, $I_D = -5.6\text{A}$ $V_{GS} = -4.5\text{V}$, $I_D = -2.8\text{A}$
Forward Transconductance (1)(3)	g_{fs}		14.4		S	$V_{DS} = -15\text{V}$, $I_D = -5.6\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		1979		pF	$V_{DS} = -25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$
Output Capacitance	C_{oss}		743		pF	
Reverse Transfer Capacitance	C_{rss}		279		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		7.6		ns	$V_{DD} = -15\text{V}$, $I_D = -5.6\text{A}$ $R_G = 6.2\Omega$, $V_{GS} = -10\text{V}$
Rise Time	t_r		16.3		ns	
Turn-Off Delay Time	$t_{d(off)}$		94.6		ns	
Fall Time	t_f		39.6		ns	
Gate Charge	Q_g		36		nC	$V_{DS} = -15\text{V}$, $V_{GS} = -5\text{V}$ $I_D = -5.6\text{A}$
Total Gate Charge	Q_g		62.5		nC	$V_{DS} = -15\text{V}$, $V_{GS} = -10\text{V}$ $I_D = -5.6\text{A}$
Gate-Source Charge	Q_{gs}		4.9		nC	
Gate Drain Charge	Q_{gd}		19.6		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			-0.95	V	$T_j = 25^{\circ}\text{C}$, $I_S = -5.6\text{A}$, $V_{GS} = 0\text{V}$
Reverse Recovery Time (3)	t_{rr}		35		ns	$T_j = 25^{\circ}\text{C}$, $I_F = -5.6\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge(3)	Q_{rr}		39.9		nC	

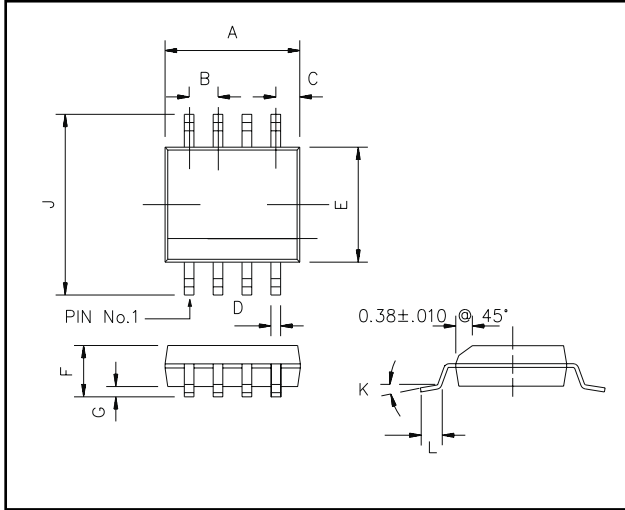
(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.

(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

ZXM66P03N8

PACKAGE DIMENSIONS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	4.80	4.98	0.189	0.196
B	1.27 BSC		0.05 BSC	
C	0.53 REF		0.02 REF	
D	0.36	0.46	0.014	0.018
E	3.81	3.99	0.15	0.157
F	1.35	1.75	0.05	0.07
G	0.10	0.25	0.004	0.010
J	5.80	6.20	0.23	0.24
K	0°	8°	0°	8°
L	0.41	1.27	0.016	0.050

ZETEX Zetex plc.
 Fields New Road, Chadderton, Oldham, OL9-8NP, United Kingdom.
 Telephone: (44)161 622 4422 (Sales), (44)161 622 4444 (General Enquiries)
 Fax: (44)161 622 4420

Zetex GmbH
 Streifeldstraße 19
 D-81673 München
 Germany
 Telefon: (49) 89 45 49 49 0
 Fax: (49) 89 45 49 49 49

Zetex Inc.
 47 Mall Drive, Unit 4
 Commack NY 11725
 USA
 Telephone: (631) 543-7100
 Fax: (631) 864-7630

Zetex (Asia) Ltd.
 3701-04 Metroplaza, Tower 1
 Hing Fong Road,
 Kwai Fong, Hong Kong
 Telephone: (852) 26100 611
 Fax: (852) 24250 494

These are supported by
 agents and distributors in
 major countries world-wide
 ©Zetex plc 2000

Internet <http://www.zetex.com>

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

ZETEX

PROVISIONAL ISSUE A - MAY 2001